



- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent Cdv/dt effect decline
- ★ Advanced high cell density Trench technology

CST6003A Product Summary

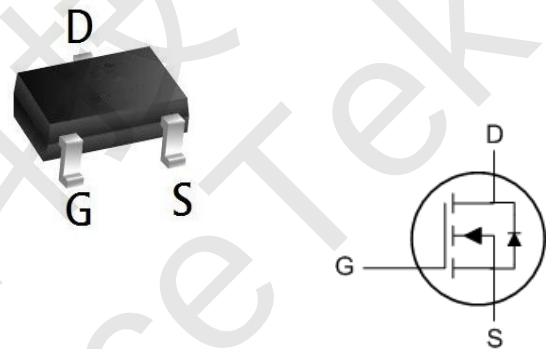


BVDSS	RDSON	ID
60V	62 mΩ	3A

CST6003A Description

The CST6003A is the high cell density trenched N-ch MOSFETs, which provides excellent RDSON and efficiency for most of the small power switching and load switch applications. The CST6003A meet the RoHS and Green Product requirement with full function reliability approved.

CST6003A SOT23 Pin Configuration



■ CST6003A Absolute Maximum Ratings (T_A=25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		V _{DS}	60	V
Gate-source Voltage		V _{GS}	±20	V
Drain Current	T _A =25°C	I _D	3	A
	T _A =100°C		1.9	
Pulsed Drain Current ^A		I _{DM}	18	A
Total Power Dissipation ^B	T _A =25°C	P _D	1.2	W
	T _A =100°C		0.45	
Junction and Storage Temperature Range		T _J , T _{STG}	-55~+150	°C

■ CST6003A Thermal resistance

Parameter		Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient ^C	Steady-State	R _{θJA}	85	105	°C/W



CST6003A N-Ch 60V Fast Switching MOSFETs

■ CST6003A Electrical Characteristics (T_J=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D =250μA	60	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V, V _{GS} =0V	-	-	1	μA
		V _{DS} =60V, V _{GS} =0V, T _j =150°C	-	-	100	
Gate-Body Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} =0V	-	-	±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D =250μA	0.9	1.35	2	V
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =10V, I _D =3A	-	62	85	mΩ
		V _{GS} =4.5V, I _D =3A	-	70	95	
Diode Forward Voltage	V _{SD}	I _S =3A, V _{GS} =0V	-	0.85	1.2	V
Gate resistance	R _G	f=1MHz, Open drain	-	2	-	Ω
Maximum Body-Diode Continuous Current	I _S		-	-	3	A
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{DS} =30V, V _{GS} =0V, f=1MHz	-	500	-	pF
Output Capacitance	C _{oss}		-	28	-	
Reverse Transfer Capacitance	C _{rss}		-	22	-	
Switching Parameters						
Total Gate Charge	Q _g	V _{GS} =10V, V _{DS} =30V, I _D =3A	-	10	-	nC
Gate-Source Charge	Q _{gs}		-	1.7	-	
Gate-Drain Charge	Q _{gd}		-	2.1	-	
Reverse Recovery Charge	Q _{rr}	I _F =3A, di/dt=100A/us	-	7	-	nC
Reverse Recovery Time	t _{rr}		-	33	-	ns
Turn-on Delay Time	t _{D(on)}	V _{GS} =10V, V _{DD} =30V, R _L =20Ω R _{GEN} =3Ω	-	3.6	-	ns
Turn-on Rise Time	t _r		-	17.6	-	
Turn-off Delay Time	t _{D(off)}		-	13	-	
Turn-off fall Time	t _f		-	23	-	

A. Repetitive rating; pulse width limited by max. junction temperature.

B. P_d is based on max. junction temperature, using junction-case thermal resistance.

C. The value of R_{θJA} is measured with the device mounted on the minimum recommend pad size, in the still air environment with T_A=25°C. The maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.



■ CST6003A Typical Electrical and Thermal Characteristics Diagrams

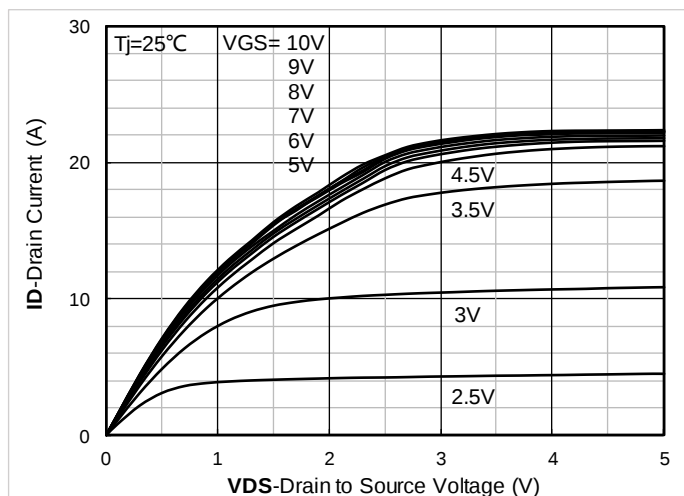


Figure 1. Output Characteristics

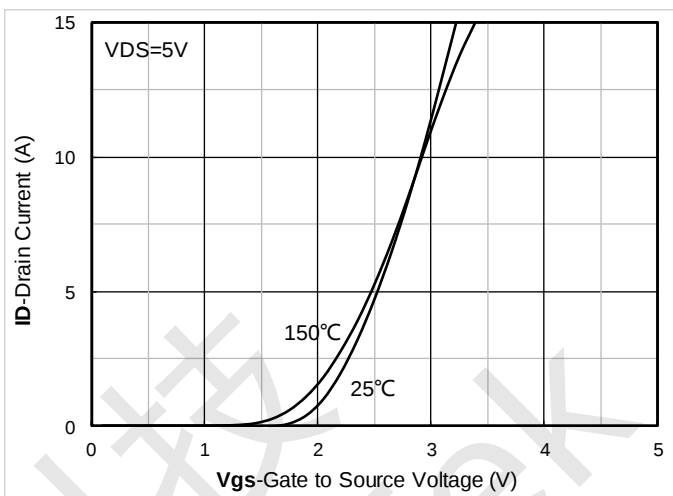


Figure 2. Transfer Characteristics

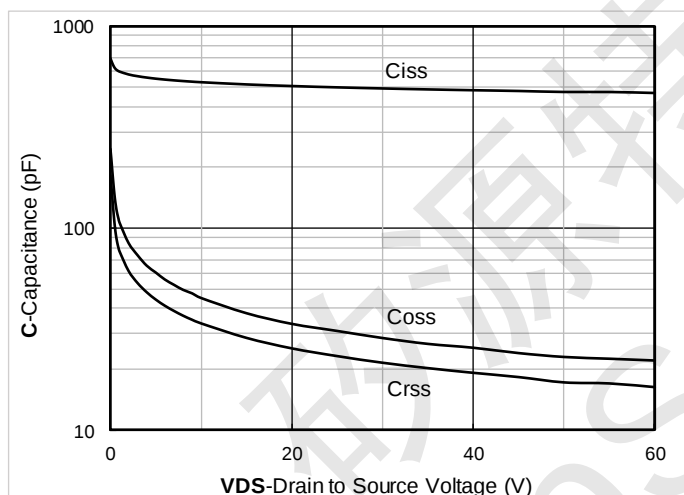


Figure 3. Capacitance Characteristics

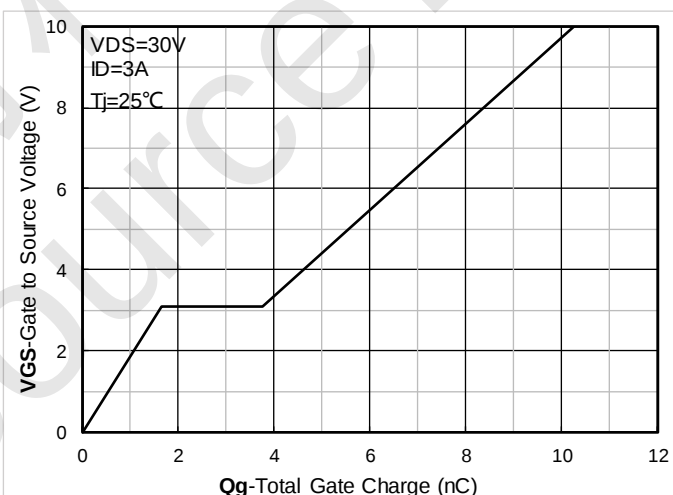


Figure 4. Gate Charge

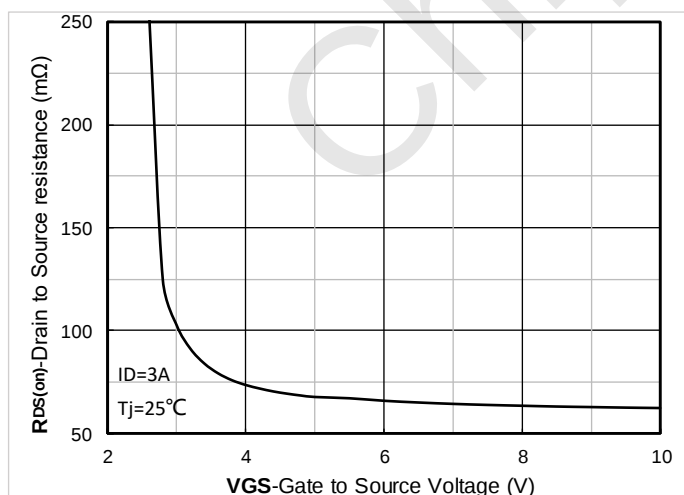


Figure 5. On-Resistance vs Gate to Source Voltage

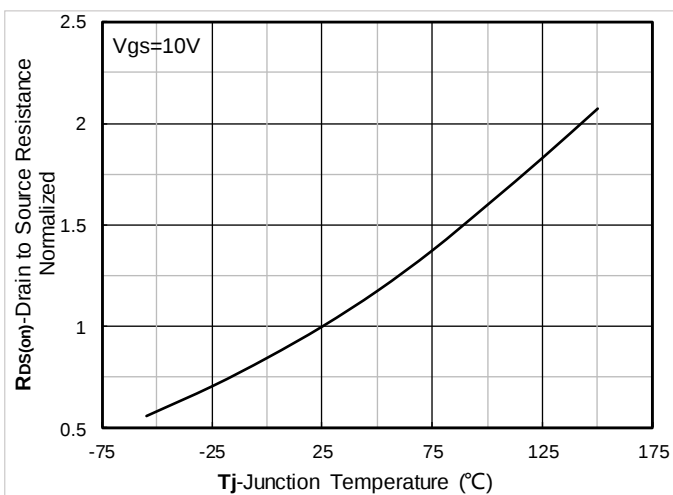


Figure 6. Normalized On-Resistance

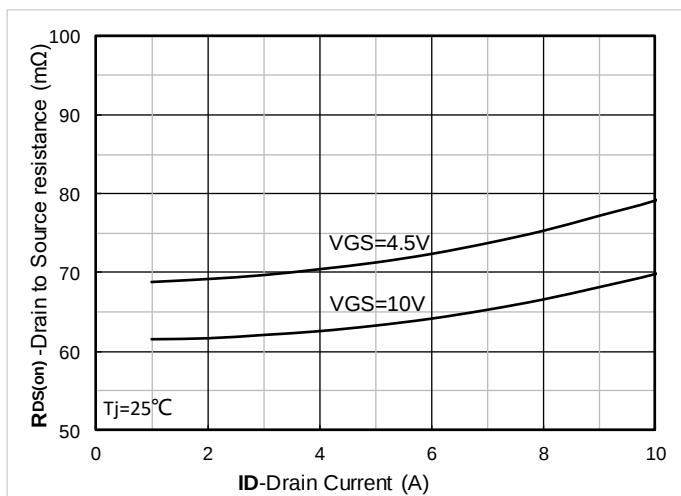


Figure 7. RDS(on) VS Drain Current

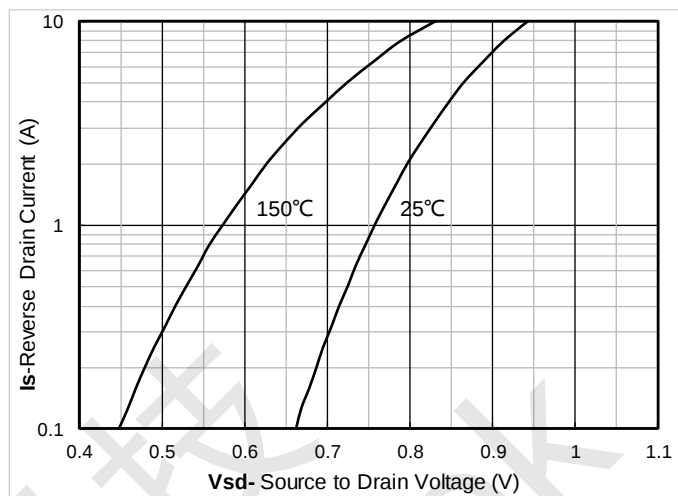


Figure 8. Forward characteristics of reverse diode

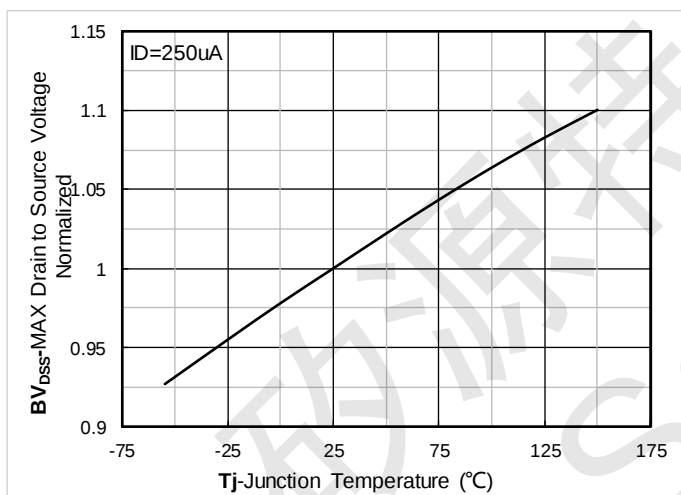


Figure 9. Normalized breakdown voltage

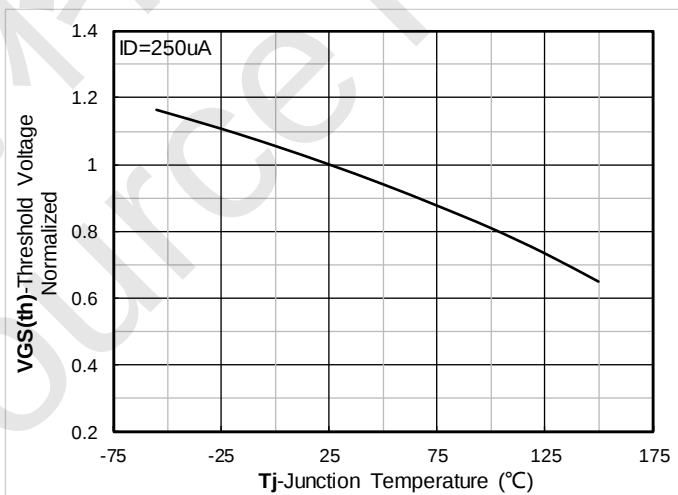


Figure 10. Normalized Threshold voltage

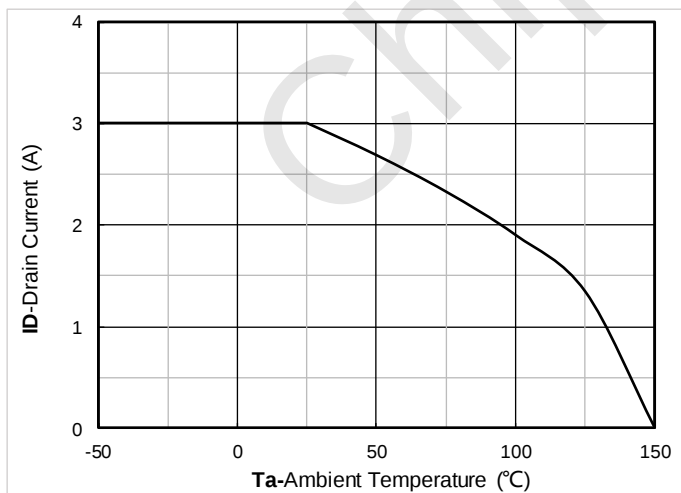


Figure 11. Current dissipation

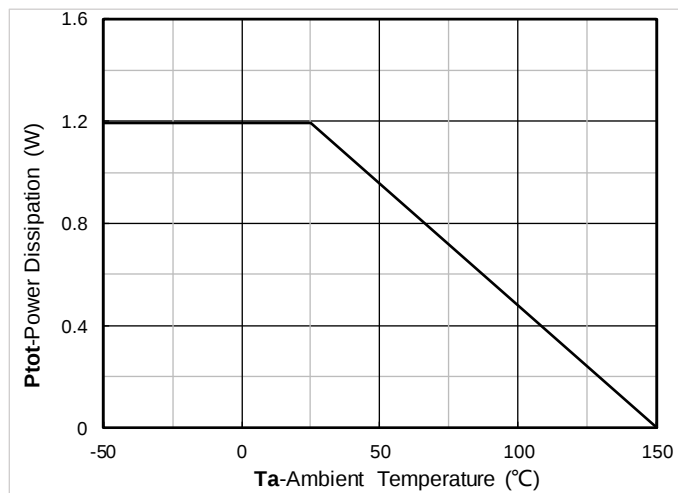


Figure 12. Power dissipation

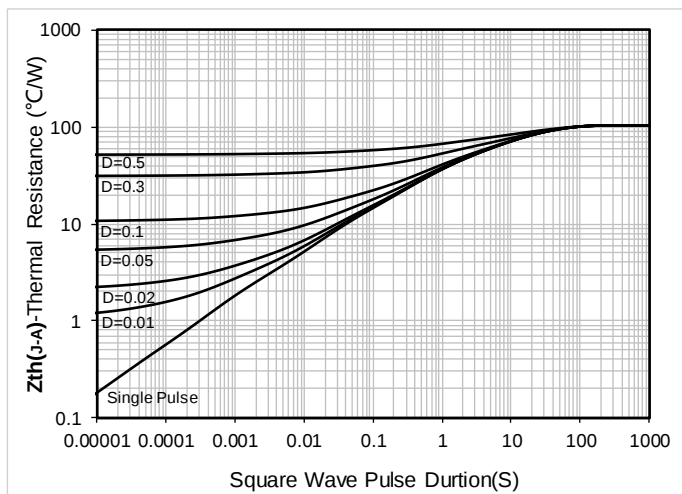


Figure 13. Maximum Transient Thermal Impedance

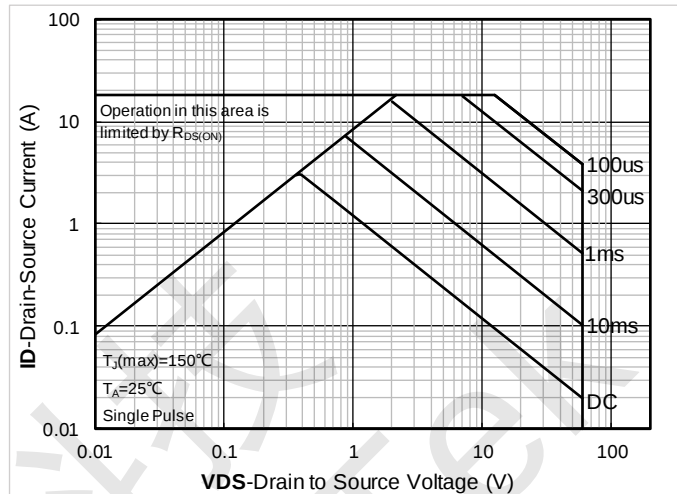


Figure 14. Safe Operation Area

■ CST6003A Test Circuits & Waveforms

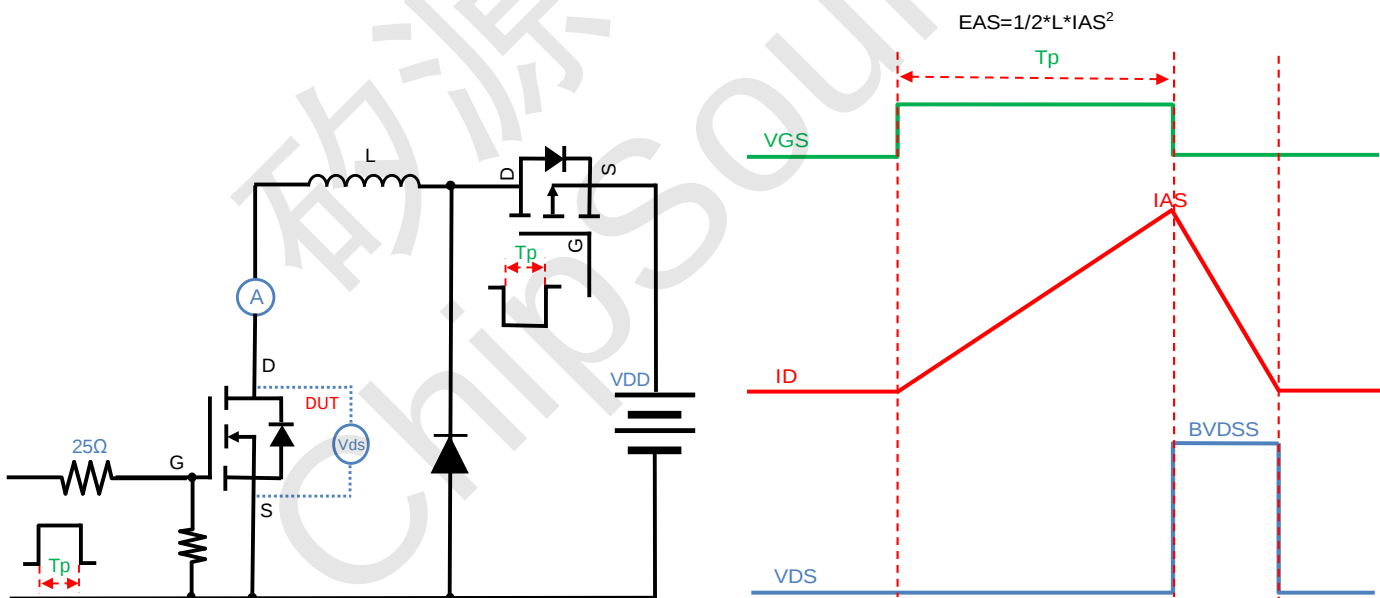


Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform

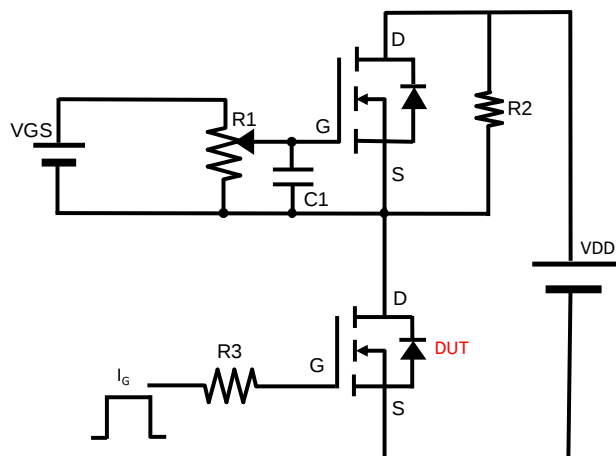


Figure B. Gate Charge Test Circuit & Waveform

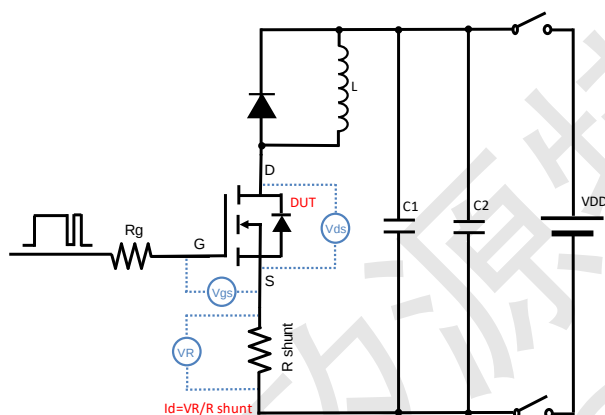


Figure C. Resistive Switching Test Circuit & Waveform

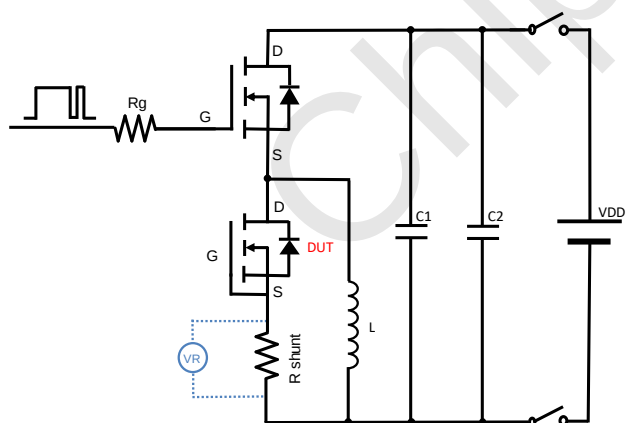
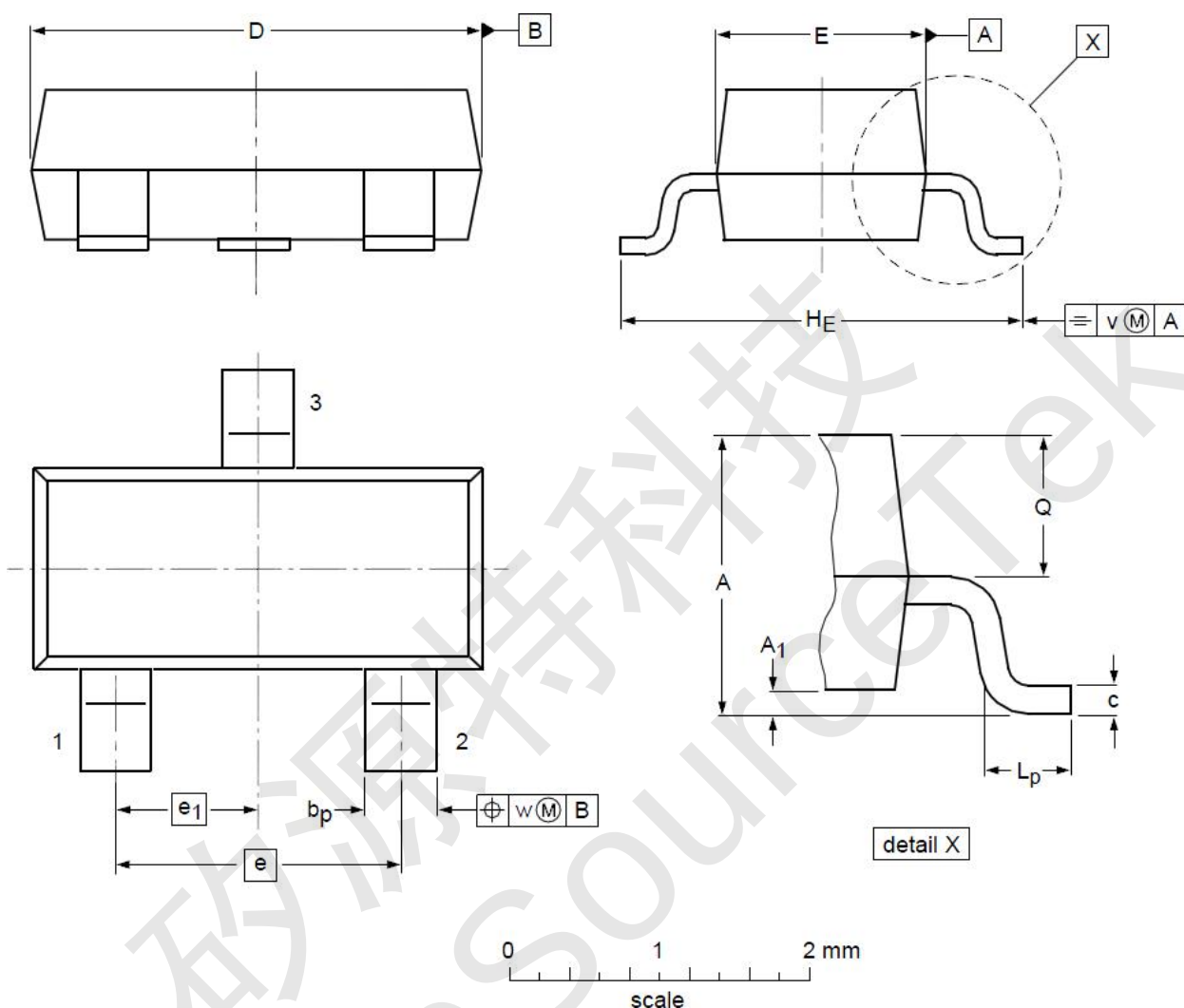


Figure D. Diode Recovery Test Circuit & Waveform



CST6003A SOT23 Mechanical Data



DIMENSIONS (unit : mm)

Symbol	Min	Typ	Max	Symbol	Min	Typ	Max
A	0.90	1.01	1.15	A ₁	0.01	0.05	0.10
b _p	0.30	0.42	0.50	c	0.08	0.13	0.15
D	2.80	2.92	3.00	E	1.20	1.33	1.40
e	--	1.90	--	e ₁	--	0.95	--
H _E	2.25	2.40	2.55	L _p	0.30	0.42	0.50
Q	0.45	0.49	0.55	v	--	0.20	--
w	--	0.10	--				